2STW4468

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 140 V
- Complementary to 2STW1695 W.DZSC.COM
- Fast-switching speed
- Typical $f_t = 20 \text{ MHz}$
- Fully characterized at 125 °C

Applications

Audio power amplifier

Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stage.

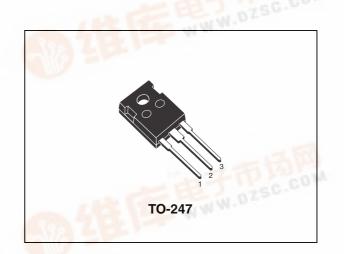


Figure 1. Internal schematic diagram

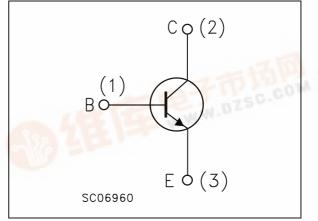


Table 1. **Device summary**

	J	Packaging	Package	Marking	Order code
2STW4468 2STW4468 TO-247 Tube		Tube	TO-247	2STW4468 2STW4468	



1 Electrical ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	200	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	140	V
V _{EBO}	Emitter-base voltage (I _C = 0)	6	V
Ι _C	Collector current	10	А
I _{СМ}	Collector peak current (t _P < 5 ms)	20	А
P _{tot}	Total dissipation at $T_c = 25 \ ^{\circ}C$	100	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 2. Absolute maximum rating

Table 3.Thermal data

Symbo	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.25	°C/W

2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Table 4. Electrical characteristics							
Symbol	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = 200 V				0.1	μA
I _{EBO}	Emitter cut-off current $(I_{\rm C} = 0)$	V _{EB} = 6 V				0.1	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA		140			V
V _{(BR)CBO}	Collector-base breakdown voltage $(I_E = 0)$	I _C = 100 μΑ		200			V
V _{(BR)EBO (1)}	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA		6			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 5 A I _C = 7 A	l _B = 500 mA l _B = 700 mA			0.5 0.7	V V
V_{BE}	Base-emitter voltage	$V_{CE} = 5 V$	I _C = 5 A			1.3	V
h _{FE}	DC current gain	I _C = 3 A I _C = 5 A	-	70 50		140	
f _T	Transition frequency	I _C = 0.5 A	V _{CE} = 12 V		20		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V	f = 1 MHz		150		pF
	Resistive Load						
t _{on}	Turn-on time	$V_{CC} = 60 V$	I _C = 5 A		0.22		μs
t _{stg}	Storage time	$I_{B1} = -I_{B2} = 0.5$	5 A		4.3		μs
t _f	Fall time				0.5		μs

Table 4.	Electrical	characteristics

1. Pulse duration = 300 $\mu s,$ duty cycle ≤ 1.5 %

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2.1 Electrical characteristics (curves)

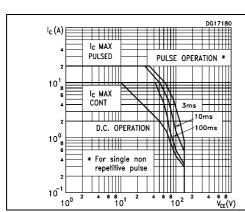


Figure 2. Safe operating area



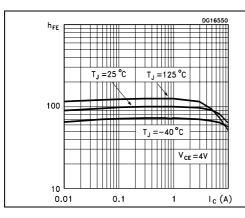


Figure 6. Base-emitter voltage

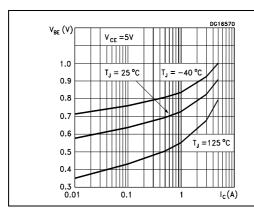


Figure 3. Output characteristics

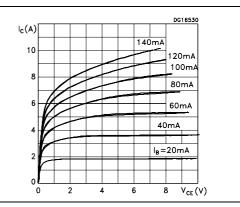


Figure 5. Collector-emitter saturation voltage

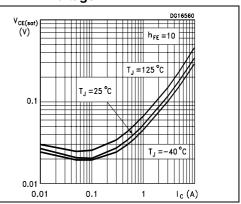
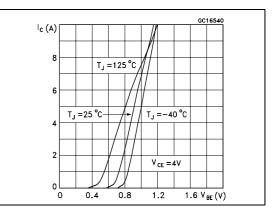
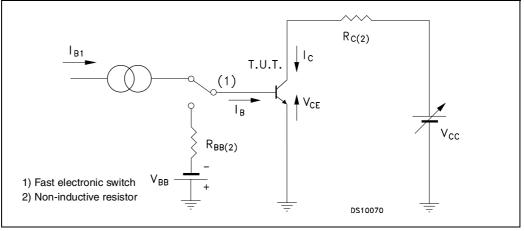


Figure 7. Base-emitter voltage



2.2 Test circuit







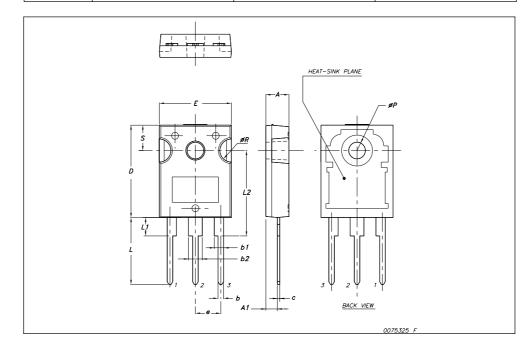
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



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TO-247 Mechanical data			
Dim.		mm.	1
	Min.	Тур	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



4 Revision history

Table 5.	Document revision	history
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Date	Revision	Changes
23-Oct-2006	1	Initial release
09-Feb-2007	2	New graphics
20-Feb-2007	3	Document status promoted from preliminary data to datasheet.
13-Oct-2008	4	Content reworked to improve readability, no technical changes.



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